

查询"SFT700D-28Q"供应商

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

SFT700D-28Q

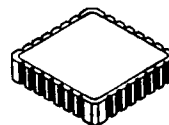
Designer's Data Sheet

FEATURES:

- **Eutectic Die Attach, Hermetic Package**
- **Electrical performance similar to 2N2222A and 2N2907A.**
- **Hermetically Sealed Surface Mount Package**
- **Fast Complimentary Switching**
- **TX, TXV and Space Level Screening Available**

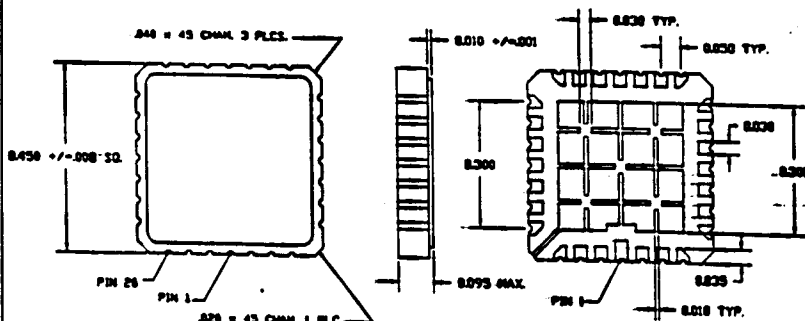
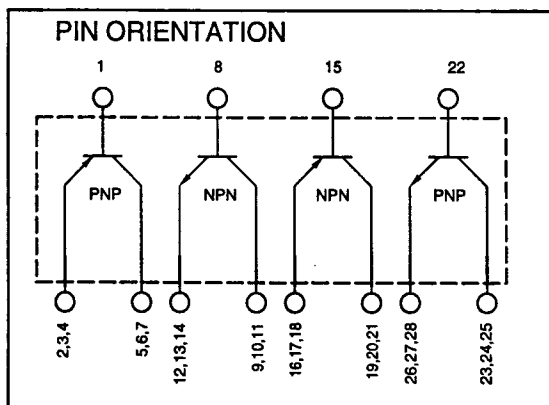
Dual 800mA, 75 V-NPN and Dual 600mA, 60 V-PNP Transistor*

28 PIN CLCC



MAXIMUM RATINGS (Per Transistor)

CHARACTERISTIC	SYMBOL	NPN VALUE	PNP VALUE	UNIT
Collector-Emitter Voltage	V _{CEO}	40	60	V
Collector-Base Voltage	V _{CBO}	75	60	V
Emitter-Base Voltage	V _{EB0}	6.0	5.0	V
Collector Current	I _C	800	600	mA
NPN to PNP Isolation Voltage	I _V	500		V
Total Device Dissipation @ TC= 25 °C (All four transistors)	P _D	4.8		W
Operating and Storage Temperature	T _J , T _{stj}	-55 to +200		°C
Thermal Resistance, Junction to Case (All four transistors)	R _{θJC}	20		°C/W

PACKAGE OUTLINE: 28 PIN QUAD CLCC

NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET: XN0035 A

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**SOLID STATE DEVICES, INC**14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**ELECTRICAL CHARACTERISTICS (Per Transistor) @ $T_J=25^{\circ}\text{C}$ (Unless Otherwise Specified)**

RATING	SYMBOL	DUAL NPN		DUAL PNP		UNIT
		MIN	MAX	MIN	MAX	
Collector-Emitter Breakdown Voltage ($I_C = 10.0\text{mA}$, $I_B = 0\text{A}$)	BV_{CEO}	50	---	60	---	V
Collector-Base Breakdown Voltage ($I_C = 10.0\mu\text{A}$, $I_E = 0\text{A}$)	BV_{CBO}	75	---	60	---	V
Emitter-Base Breakdown Voltage ($I_E = 10\mu\text{A}$, $I_C = 0\text{A}$)	BV_{EBO}	6	---	5	---	V
Collector Cutoff Current ($V_{CE} = 60\text{Vdc}$) ($V_{CE} = 50\text{Vdc}$) ($V_{CE} = 60\text{Vdc}$, 150°C) ($V_{CE} = 50\text{Vdc}$, 150°C)	I_{CBO}	---	10	---	10	nA μA
Collector Cutoff Current ($V_{CE} = 50\text{V}$) ($V_{CE} = 30\text{V}$)	I_{CES}	---	50	---	50	nA
Emitter Cutoff Current ($V_{EB} = 4\text{Vdc}$ for NPN, $V_{EB} = 3.5\text{Vdc}$ for PNP)	I_{EBO}	---	10	---	50	nA
DC Current Gain ($I_C = 100\mu\text{A}$, $V_{CE} = 10\text{Vdc}$) ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$) ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$) ($I_C = 150\text{mA}$, $V_{CE} = 10\text{Vdc}$) ($I_C = 500\text{mA}$, $V_{CE} = 10\text{Vdc}$) ($I_C = 10\text{mA}$, $V_{CE} = 10\text{Vdc}$, -55°C) ($I_C = 1.0\text{mA}$, $V_{CE} = 10\text{Vdc}$, -55°C)	H_{FE}	50 75 100 100 30 35 ---	---	75 100 100 100 50 ---	---	450 ---
Small Signal Current Gain ($V_{CE} = 10\text{Vdc}$, $I_C = 1\text{mA}$, $f = 1\text{kHz}$)	h_{fe}	50	---	100	---	
Collector-Emitter Saturation Voltage ($I_C = 150\text{mA}$, $I_B = 15\text{mA}$) ($I_C = 500\text{mA}$, $I_B = 50\text{mA}$)	$V_{CE(SAT)}$	---	0.3 1.0	---	0.4 1.6	V
Base-Emitter Saturation Voltage ($I_C = 150\text{mA}$, $I_B = 15\text{mA}$) ($I_C = 500\text{mA}$, $I_B = 50\text{mA}$)	$V_{BE(SAT)}$	0.6 ---	1.2 2.0	---	1.3 2.6	V
Magnitude of Small Signal Short Circuit Current Gain ($I_C = 20\text{mA}$, $V_{CE} = 20\text{Vdc}$, $f = 100\text{MHz}$) ($I_C = 50\text{mA}$, $V_{CE} = 20\text{Vdc}$, $f = 100\text{MHz}$)	$ h_{fe} $	2.5 ---	---	2	---	
Output Capacitance ($V_{CB} = 10\text{Vdc}$, $I_E = 0\text{A}$, $f = 1\text{MHz}$)	C_{ob}	---	8	---	8	pF
Input Capacitance ($V_{BE} = 0.5\text{Vdc}$, $I_E = 0\text{A}$, $f = 1\text{MHz}$) ($V_{BE} = 2.0\text{Vdc}$, $I_E = 0\text{A}$, $f = 1\text{MHz}$)	C_{ib}	---	25 ---	---	30	pF
Turn On Time Turn Off Time	t_{on} t_{f}	---	35 300	---	45 300	nsec

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.